conditions of process characterization, including but not limited to actual etch conditions or actual film deposition conditions.

[75 FR 74818, Dec. 1, 2010, as amended at 77 FR 10381, Feb. 22, 2012]

TABLE I–1 TO SUBPART I OF PART 98—DEFAULT EMISSION FACTORS FOR THRESHOLD APPLICABILITY DETERMINATION

Product type	Emission factors EF_i					
	CF_4	C_2F_6	CHF_3	C_3F_8	NF_3	SF_6
Semiconductors (kg/m^2)	0.90	1.00	0.04	0.05	0.04	0.20
LCD (g/m^2)	0.50	NA	NA	NA	0.90	4.00
MEMS (kg/m^2)	NA	NA	NA	NA	NA	1.02

Notes: NA denotes not applicable based on currently available information.

TABLE I–2 TO SUBPART I OF PART 98—EXAMPLES OF FLUORINATED GHGS AND FLUORINATED HEAT TRANSFER FLUIDS USED BY THE ELECTRONICS INDUSTRY

Product type	Fluorinated GHGs and fluorinated heat transfer fluids used during manufacture
Electronics	CF_4, C_2F_6, C_3F_8, c-C_4F_8, c-C_4F_8O, C_4F_6, C_5F_8, CHF_3, CH_2F_2, NF_3, SF_6, and fluorinated HTFs (CF_3-(O-CF(CF_3)-CF_2)$_n$-(O-CF_2)$_m$-O-CF_3, C_nF_{2n+2}, $C_nF_{2n+1}(O)C_mF_{2m+1}$, $C_nF_{2n}O$, $(C_nF_{2n+1})_{3N}$).

[77 FR 10381, Feb. 22, 2012]

TABLE I–3 TO SUBPART I OF PART 98—DEFAULT EMISSION FACTORS ($1–U_{ij}$) FOR GAS UTILIZATION RATES (U_{ij}) AND BY-PRODUCT FORMATION RATES (B_{ijk}) FOR SEMICONDUCTOR MANUFACTURING FOR 150MM AND 200 MM WAFER SIZES

Process type/Sub-type	Process gas i										
	CF_4	C_2F_6	CHF_3	CH_2F_2	C_3F_8	c-C_4F_8	NF_3	SF_6	C_4F_6	C_5F_8	C_4F_8O
Plasma Etching											
$1–U_i$	0.69	0.56	0.38	0.093	NA	0.25	0.038	0.20	0.14	NA	NA
BCF_4	NA	0.23	0.026	0.021	NA	0.19	0.0040	NA	0.13	NA	NA
BC_2F_6	NA	NA	NA	NA	NA	0.084	NA	NA	0.12	NA	NA
BC_3F_8	NA	NA	NA	NA	NA	NA	NA	NA	NA	NA	NA
Chamber Cleaning											
In situ plasma cleaning:											
$1–U_i$	0.92	0.55	NA	NA	0.40	0.10	0.18	NA	NA	NA	0.14
BCF_4	NA	0.19	NA	NA	0.20	0.11	0.011	NA	NA	NA	0.13
BC_2F_6	NA	NA	NA	NA	NA	NA	NA	NA	NA	NA	0.030
BC_3F_8	NA	NA	NA	NA	NA	NA	NA	NA	NA	NA	NA
Remote plasma cleaning:											
$1–U_i$	NA	NA	NA	NA	NA	NA	0.018	NA	NA	NA	NA
BCF_4	NA	NA	NA	NA	NA	NA	0.0047	NA	NA	NA	NA
BC_2F_6	NA	NA	NA	NA	NA	NA	NA	NA	NA	NA	NA
BC_3F_8	NA	NA	NA	NA	NA	NA	NA	NA	NA	NA	NA
In situ thermal cleaning:											
$1–U_i$	NA	NA	NA	NA	NA	NA	NA	NA	NA	NA	NA
BCF_4	NA	NA	NA	NA	NA	NA	NA	NA	NA	NA	NA
BC_2F_6	NA	NA	NA	NA	NA	NA	NA	NA	NA	NA	NA
BC_3F_8	NA	NA	NA	NA	NA	NA	NA	NA	NA	NA	NA
Wafer Cleaning											
$1–U_i$	0.77	NA	NA	0.24	NA	NA	0.23	0.20	NA	NA	NA
BCF_4	NA	NA	NA	NA	NA	NA	NA	NA	NA	NA	NA
BC_2F_6	NA	NA	NA	NA	NA	NA	NA	NA	NA	NA	NA
BC_3F_8	NA	NA	NA	NA	NA	NA	NA	NA	NA	NA	NA

Notes: NA denotes not applicable based on currently available information.